

# Silicon Bridge Rectifier

 $V_{RRM} = 50\text{ V} - 1000\text{ V}$ 
 $I_F = 1.5\text{ A}$ 

## Features

- Types up to 1000 V  $V_{RRM}$
- Ideal for printed circuit board
- Low forward voltage drop
- High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375" lead length
- Low leakage current

**WOM Package**


## Mechanical Data

Case: Plastic

Polarity: Color band on body denotes cathode

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-202

Method 208 guaranteed

Weight: 1.07 grams, 0.038 oz

## Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	W06M	W08M	W10M	Unit
Repetitive peak reverse voltage	$V_{RRM}$		600	800	1000	V
RMS reverse voltage	$V_{RMS}$		420	560	700	V
DC blocking voltage	$V_{DC}$		600	800	1000	V
Continuous forward current	$I_F$	$T_C \leq 50\text{ °C}$	1.5	1.5	1.5	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	50	50	50	A
Operating temperature	$T_j$		-65 to 125	-65 to 125	-65 to 125	°C
Storage temperature	$T_{stg}$		-65 to 150	-65 to 150	-65 to 150	°C

## Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	W06M	W08M	W10M	Unit
Diode forward voltage	$V_F$	$I_F = 1\text{ A}$ , $T_j = 25\text{ °C}$	1	1	1	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$	10	10	10	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 100\text{ °C}$	500	500	500	

## Thermal characteristics

Parameter	Symbol	Conditions	W06M	W08M	W10M	Unit
Thermal resistance, junction - case	$R_{thJC}$		36.00	36.00	36.00	°C/W

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

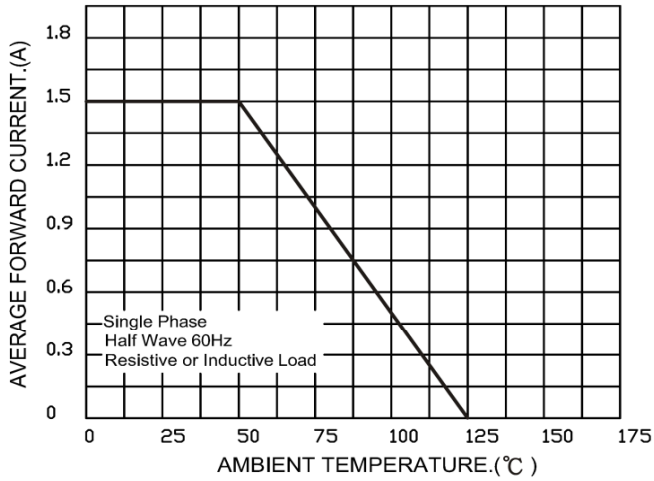


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

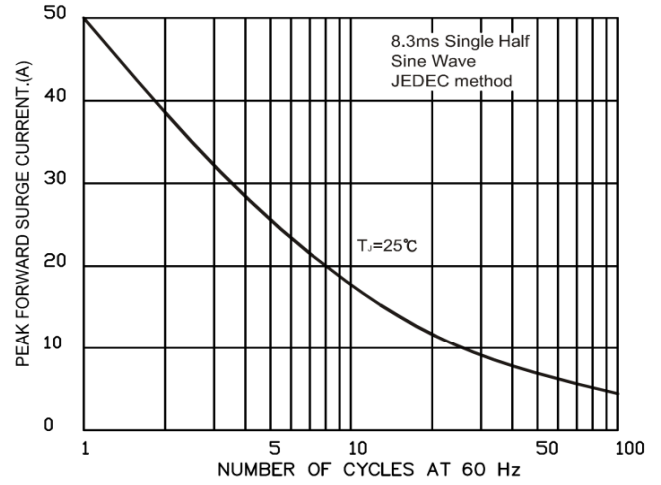


FIG.3-TYPICAL FORWARD CHARACTERISTICS

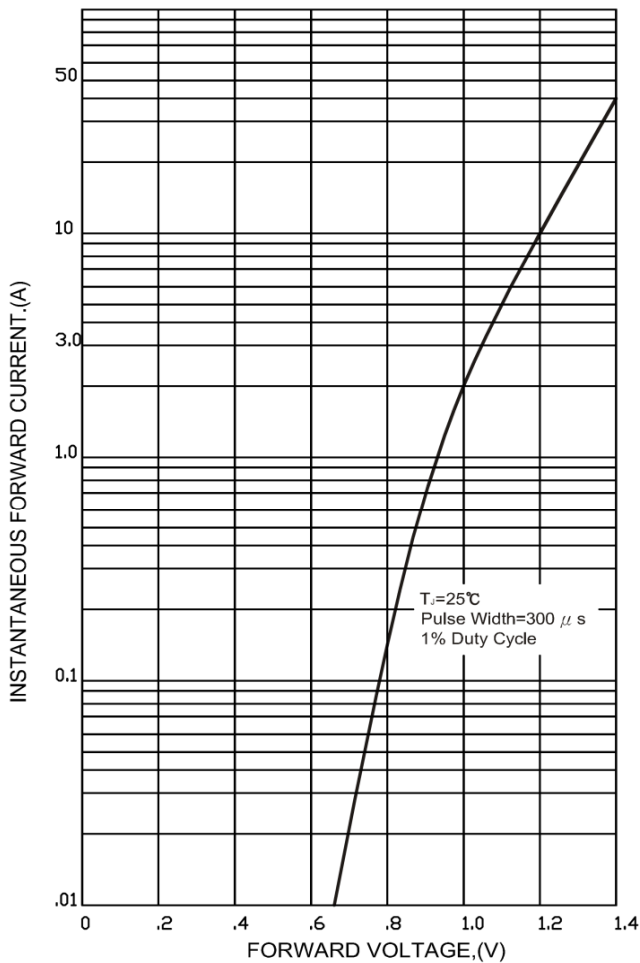


FIG.4-TYPICAL REVERSE CHARACTERISTICS

